

## **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

The NCEP60T18 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

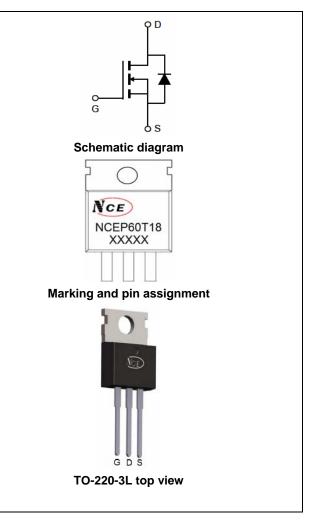
#### **General Features**

- $V_{DS} = 60V, I_{D} = 180A$ 
  - $R_{DS(ON)} < 3.2 \text{m}\Omega$  @  $V_{GS} = 10 \text{V}$  (Typ:2.8 m $\Omega$ )
- Excellent gate charge x R<sub>DS(on)</sub> product
- Very low on-resistance R<sub>DS(on)</sub>
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

#### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP60T18	NCEP60T18	TO-220-3L	-	-	-

Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	60	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	V	
Drain Current-Continuous (Silicon Limited)	I <sub>D</sub>	180	Α	
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	126	Α	
Pulsed Drain Current	I <sub>DM</sub>	720	А	
Maximum Power Dissipation	P <sub>D</sub>	220	W	
Derating factor		1.47	W/°C	
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	1036	mJ	
Drain Source voltage slope, V <sub>DS</sub> ≤48V,	dv/dt	50	V/ns	
Reverse diode dv/dt, V <sub>DS</sub> ≤48 V, I <sub>SD</sub> <i<sub>D</i<sub>	dv/dt	15	V/ns	
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$ C	

# NCEP60T18

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	0.68	°C/W
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Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	<sub>S</sub> =0V I <sub>D</sub> =250μA 60		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =40A	-	2.8	3.2	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =40A	50	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ 00\/\\ 0\/	-	4500	-	PF
Output Capacitance	Coss	$V_{DS}$ =30V, $V_{GS}$ =0V, F=1.0MHz	-	965	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	r=1.0lvln2	-	24	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	6	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30 $V$ , $I_D$ =40 $A$	-	11	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}\text{=}10V,R_{G}\text{=}4.7\Omega$	-	23	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3	-	nS
Total Gate Charge	Qg	\/ -20\/   -404	-	70	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=30V,I_{D}=40A,$	-	18.6	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	15.3	-	nC
Drain-Source Diode Characteristics	<u> </u>					
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =40A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	180	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C$ , $I_F = I_S$	-	50		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	66		nC

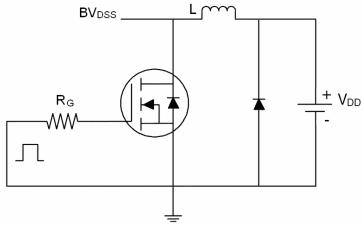
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=30V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$

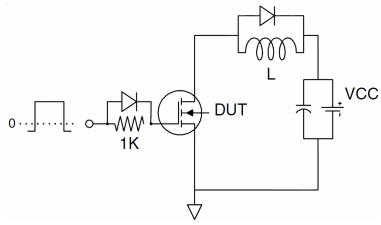


## **Test Circuit**

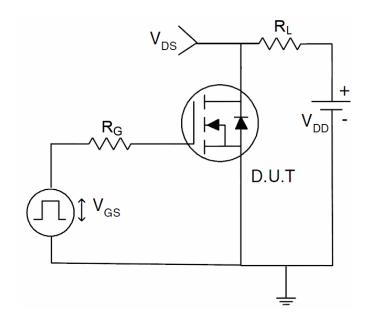
## 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

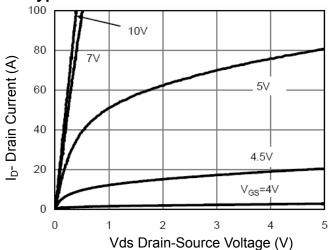


## 3) Switch Time Test Circuit

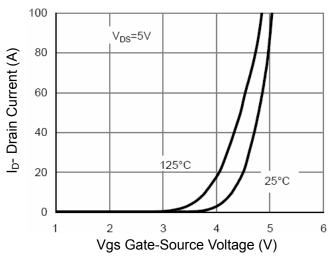




### **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

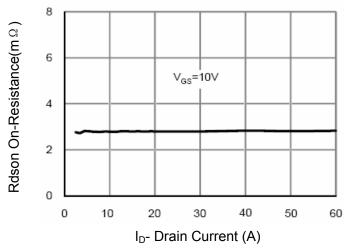
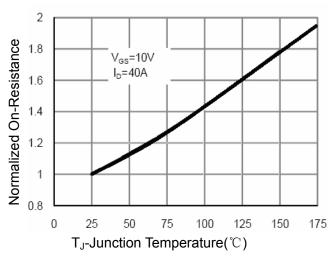


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

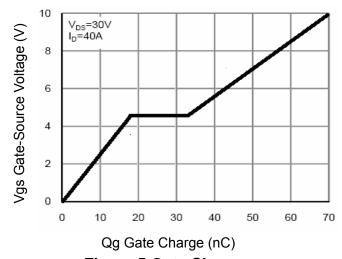


Figure 5 Gate Charge

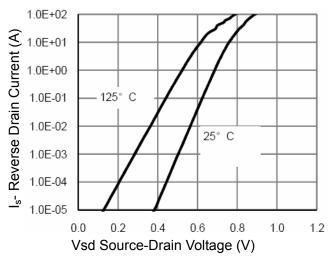


Figure 6 Source- Drain Diode Forward



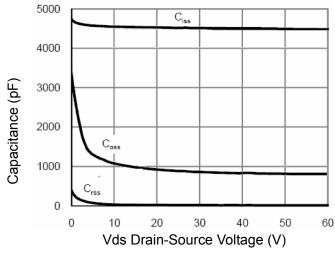


Figure 7 Capacitance vs Vds

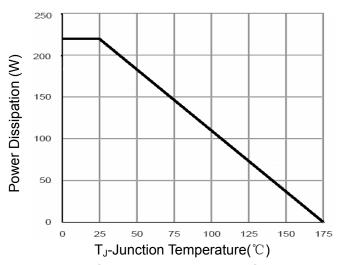
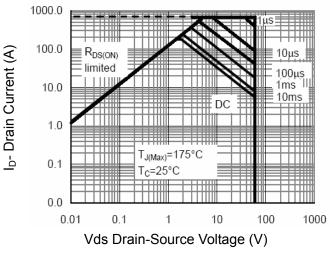


Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

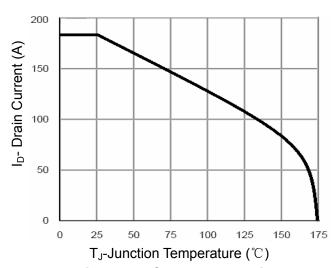


Figure 10 Current De-rating

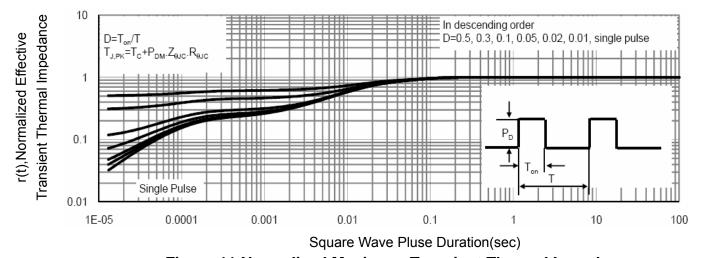
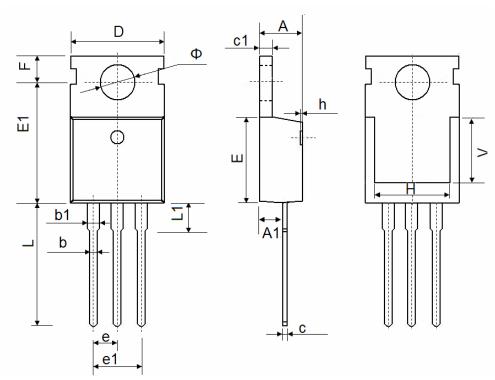


Figure 11 Normalized Maximum Transient Thermal Impedance



## **TO-220-3L Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.54	0 TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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